

PTO/SB/08A (05-03)

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STATEMENT BY APPLICANT**

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Complete if Known

Application Number	10/649,566
Filing Date	August 27, 2003
First Named Inventor	Ko, et al.
Art Unit	TBD 2813
Examiner Name	TBD DOLAN
Attorney Docket Number	TSM02-1383

Sheet 2 of 2**U.S. PATENT DOCUMENTS**

Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
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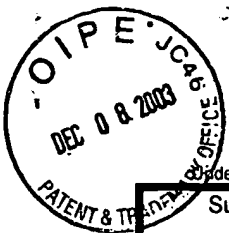
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
JMB	A	SHAREEF, I.A., et al., "Subatmospheric Chemical Vapor Deposition Ozone/TEOS Process for SiO ₂ Trench Filling", J. Vac. Sci. Technol. B 13(4), Jul/Aug 1995, pp. 1888-1892, 1995 American Vacuum Society.	
JMB	B	NGUYEN S.V., "High-Density Plasma Chemical Vapor Deposition of Silicon-Based Dielectric Films for Integrated Circuits", IBM Journal of Research and Development, vol. 43, 1/2, 1999.	
JMB	C	IBBOTSON, D.E., et al., "Plasma Processing of Low K Dielectric Films", The Electrochemical Society, Inc., Washington, D.C., March 25, 2001.	
JMB	D	BEEKMANN, K, et al., "Low-k Dielectric Requirements and Zero-Overlay Compatibility", Semiconductor International October 21, 2001	
JMB	E	KALLENDER, P., "Toshiba, Fujitsu Report 100-Nanometer Process Gains", EE Times, November 8, 2001	
JMB	F	WALDFRIED, C, et al., "Plasma Curing of Porous MSQ Films", 202 nd ECS Meeting, October 20-25, 2002.	

Examiner Signature	<i>Amie M. M.</i>	Date Considered	7/29/04
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Sheet 1 of 2

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<i>MD</i>	G	LEE, H.J. et al., "Structural Characterization of Porous Low-k SiOC Thin Films Using X-ray Porosimetry," publication and date unknown.	
<i>MD</i>	H	"MEMS Thin Film Deposition Processes," MEMS and Nanotechnology Clearinghouse, author and date unknown.	
<i>MD</i>	I	USAMI, K., et al., "A Silica-Based Inter-Metal-Insulator with Low Dielectric-Constant and High Thermal Conductivity," publication and date unknown.	

Examiner Signature	<i>George M. ...</i>	Date Considered	7/29/04
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